

10 / 607,98

## Refine Search

### Search Results -

Terms	Documents
L5 and (impurity or impurities)	5

Database:

US Pre-Grant Publication Full-Text Database  
 US Patents Full-Text Database  
 US OCR Full-Text Database  
 EPO Abstracts Database  
 JPO Abstracts Database  
 Derwent World Patents Index  
 IBM Technical Disclosure Bulletins

Search:

L6

Refine Search

Recall Text

Clear

Interrupt

### Search History

DATE: Sunday, March 07, 2004 [Printable Copy](#) [Create Case](#)

**Set Name Query**  
 side by side

**Hit Count Set Name**  
 result set

*DB=USPT; PLUR=YES; OP=ADJ*

<u>L6</u>	L5 and (impurity or impurities)	5	<u>L6</u>
<u>L5</u>	L4 and pinned	24	<u>L5</u>
<u>L4</u>	L3 and (tunnel adj barrier)	26	<u>L4</u>
<u>L3</u>	L2 and ferromagnetic	37	<u>L3</u>
<u>L2</u>	L1 and MRAM	59	<u>L2</u>
<u>L1</u>	(MTJ) adj cell	68	<u>L1</u>

END OF SEARCH HISTORY

## Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 5 of 5 returned.

☐ 1. Document ID: US 6664579 B2

L6: Entry 1 of 5

File: USPT

Dec 16, 2003

US-PAT-NO: 6664579

DOCUMENT-IDENTIFIER: US 6664579 B2

TITLE: Magnetic random access memory using bipolar junction transistor

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw. De
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☐ 2. Document ID: US 6657270 B2

L6: Entry 2 of 5

File: USPT

Dec 2, 2003

US-PAT-NO: 6657270

DOCUMENT-IDENTIFIER: US 6657270 B2

TITLE: Magnetic random access memory using bipolar junction transistor, and method for fabricating the same

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw. De
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☐ 3. Document ID: US 6653704 B1

L6: Entry 3 of 5

File: USPT

Nov 25, 2003

US-PAT-NO: 6653704

DOCUMENT-IDENTIFIER: US 6653704 B1

TITLE: Magnetic memory with tunnel junction memory cells and phase transition material for controlling current to the cells

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw. De
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☐ 4. Document ID: US 6544801 B1

L6: Entry 4 of 5

File: USPT

Apr 8, 2003

US-PAT-NO: 6544801

DOCUMENT-IDENTIFIER: US 6544801 B1

TITLE: Method of fabricating thermally stable MTJ cell and apparatus

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw. De
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☐ 5. Document ID: US 6347049 B1

L6: Entry 5 of 5

File: USPT

Feb 12, 2002

US-PAT-NO: 6347049

DOCUMENT-IDENTIFIER: US 6347049 B1

TITLE: Low resistance magnetic tunnel junction device with bilayer or multilayer  
tunnel barrier

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw. De
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L5 and (impurity or impurities)	5

Display Format:  [Previous Page](#)[Next Page](#)[Go to Doc#](#)